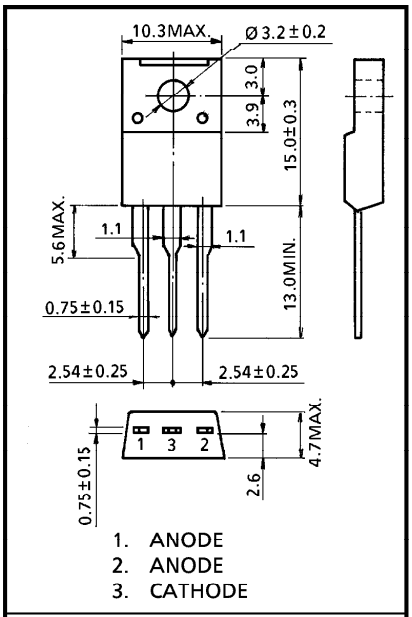
TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

10JL2CZ47

SWITCHING TYPE POWER SUPPLY APPLICATION
CONVERTER & CHOPPER APPLICATION

- Repetitive Peak Reverse Voltage : V_{RRM} = 600V
- Average Output Rectified Current : I_O = 10A
- Ultra Fast Reverse-Recovery Time : t_{rr} = 50ns (Max.)
- Low Switching Losses and Output Noise.

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	12-10C1A

Weight : 2.0g

MAXIMUM RATINGS

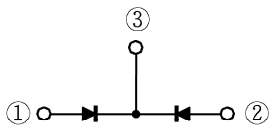
CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	600	V
Average Output Rectified Current	I_O	10	A
Peak One Cycle Surge Forward Current (Sine Wave)	I_{FSM}	50 (50Hz)	A
		55 (60Hz)	
Junction Temperature	T_j	−40~150	°C
Storage Temperature Range	T_{stg}	−40~150	°C
Screw Torque	—	0.6	N·m

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

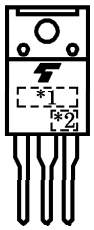
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage (Note 1)	V_{FM}	I_{FM} = 5A	—	—	2.0	V
Repetitive Peak Reverse Current (Note 1)	I_{RRM}	V_{RRM} = 600V	—	—	50	μA
Reverse Recovery Time (Note 1)	t_{rr}	I_F = 2A, di / dt = −20A / μs	—	—	50	ns
Forward Recovery Time (Note 1)	t_{fr}	I_F = 1A	—	—	150	ns
Thermal Resistance	$R_{th\,(j\text{-}c)}$	DC Total, Junction to Case	—	—	3.6	°C / W

(Note 1) A value of one cell.

POLARITY



MARKING



*1	MARK	10JL2CZ
*2	Lot Number □□ — Month (Starting from Alphabet A) — Year (Last Number of the Christian Era)	

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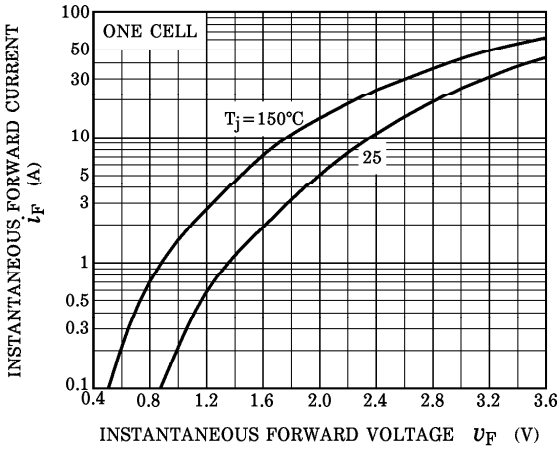
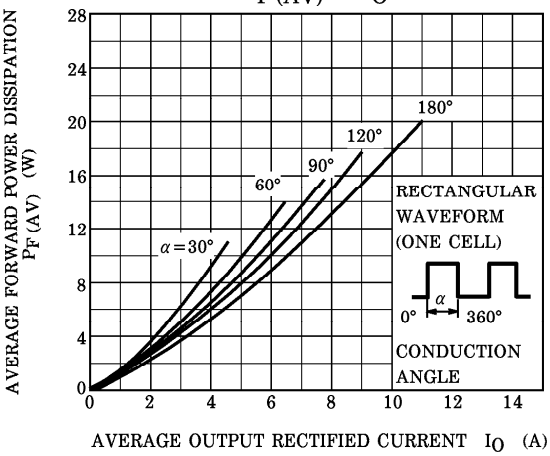
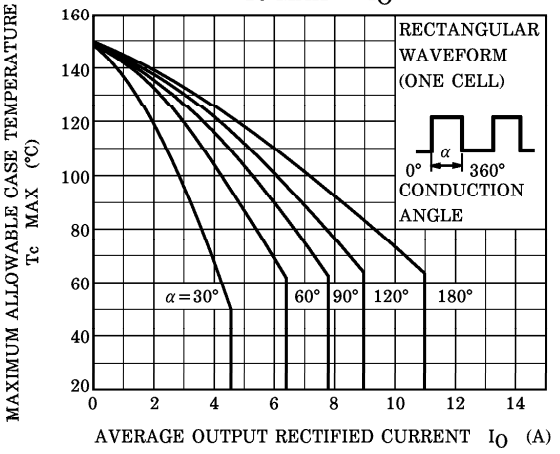
$i_F - v_F$



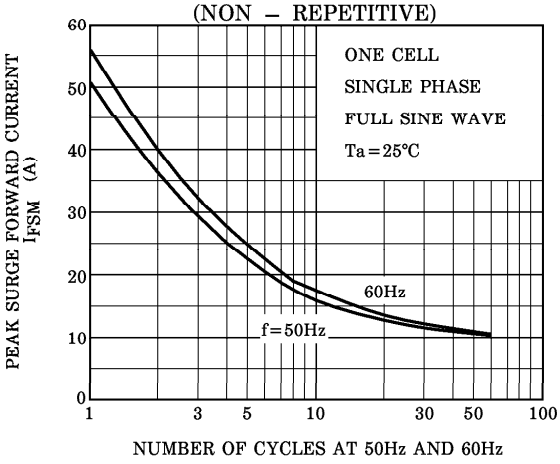
$P_{F(AV)} - I_O$



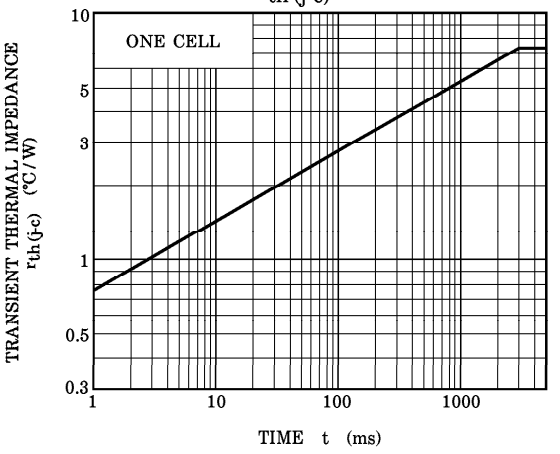
Tc MAX – I_O



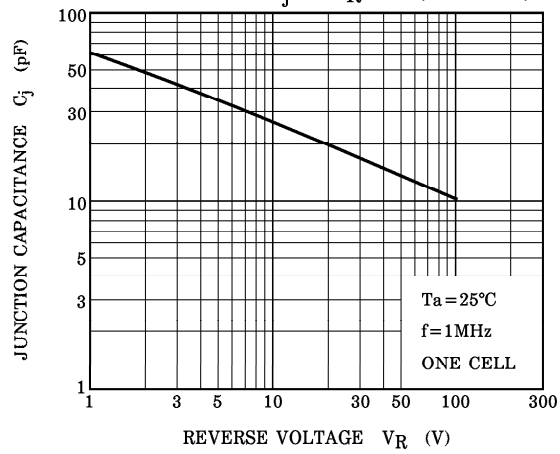
SURGE FORWARD CURRENT (NON – REPETITIVE)



$r_{th(j-c)} - t$



$C_j - V_R$ (TYPICAL)



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